

AMENDMENTS TO THE CLAIMS

Claims 1-10 (Canceled).

11. (Currently amended) A structure ~~for creating chalcogenide integrated circuit devices~~, comprising:

a first conductive material overlying a substrate;

a chalcogenide material overlying the first conductive material;

a silver material in physical contact with the chalcogenide material; and

a barrier material on and in physical contact with the silver material, the barrier material being a same material as the chalcogenide material and being essentially transparent to ultraviolet radiation.

12. (Currently amended) A structure ~~for creating chalcogenide integrated circuit devices~~, comprising:

a first electrode overlying a substrate;

a chalcogenide material overlying the first electrode;

a metal material in physical contact with the chalcogenide material; and

chalcogenide barrier material on and in physical contact with the metal material, the barrier material being a same material as the chalcogenide material and being essentially transparent to ultraviolet radiation.

13. (Previously presented) The structure of claim 12, wherein the chalcogenide barrier and the chalcogenide material are formed of the same material.

14. (Original) The structure of claim 12, wherein the same material is GeSe.

15. (Previously presented) The structure of claim 13, wherein the metal material includes silver.

Claims 16-108 (Canceled).

109. (Previously presented) The structure of claim 12 wherein the barrier material comprises germanium-selenide.

110. (Previously presented) The structure of claim 11 wherein the barrier material reduces agglomeration from the silver material.

111. (Previously presented) The structure of claim 11 wherein the silver material is formed to a thickness in a range of about 100Å to about 200Å.

112. (Previously presented) The structure of claim 11 wherein the barrier material is formed to a thickness in a range of about 20Å to about 50Å.

113. (Previously presented) The structure of claim 11 wherein the barrier material is formed to a thickness of about 30Å.

114. (Previously presented) The structure of claim 11 wherein the chalcogenide material is formed to a thickness in a range of about 500Å to about 1000Å.

Claims 115-145. (Canceled).